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dopant and profile and (capacitive or capacitance)

## Search

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### Results Key:

**JNL** = Journal or Magazine    **CNF** = Conference    **STD** = Standard

## 1 Lateral dopant profiling in MOS structures on a 100 nm scale using scanning capacitance microscopy

Slinkman, J.A.; Williams, C.C.; Abraham, D.W.; Wickramasinghe, H.K.;  
Electron Devices Meeting, 1990. Technical Digest., International , 9-12 Dec. 1990  
Pages:73 - 76

[Abstract] [PDF Full-Text (312 KB)] IEEE CNF

## 2 Two-dimensional dopant profiling of a 60 nm gate length nMOSFET using scanning capacitance microscopy

*Timp, W.; O'Malley, M.L.; Kleiman, R.N.; Garino, J.P.;*  
Electron Devices Meeting, 1998. IEDM '98 Technical Digest., International , 6-9  
Dec. 1998  
Pages:555 - 558

[\[Abstract\]](#)   [\[PDF Full-Text \(976 KB\)\]](#)   **IEEE CNF**

### 3 Monitoring oxide quality using the spread of the dC/dV peak in scanning capacitance microscopy measurements

Chim, W.K.; Wong, K.M.; Yeow, Y.T.; Hong, Y.D.; Lei, Y.; Teo, L.W.; Choi, W.K.;  
Electron Device Letters, IEEE , Volume: 24 , Issue: 10 , Oct. 2003  
Pages:667 - 670

[\[Abstract\]](#)   [\[PDF Full-Text \(304 KB\)\]](#)   **IEEE JNL**

#### 4 Inverse modeling of two-dimensional MOSFET dopant profile via capacitance of the source/drain gated diode

Chiang, C.Y.T.; Yeow, Y.T.;  
Electron Devices, IEEE Transactions on , Volume: 47 , Issue: 7 , July 2000  
Pages:1385 - 1392

[\[Abstract\]](#)   [\[PDF Full-Text \(280 KB\)\]](#)   **IEEE JNL**

## 5 Modeling study of scanning capacitance microscopy measurement for p-